

isc Silicon NPN Power Transistor

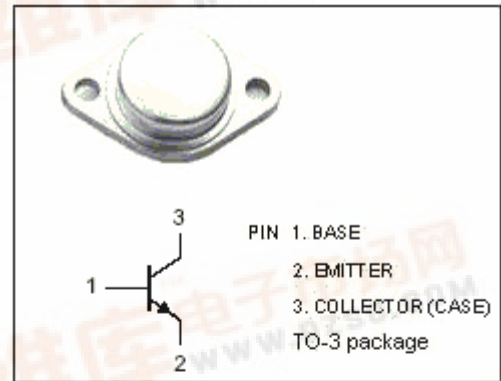
2SC2260

DESCRIPTION

- High Power Dissipation-  
:  $P_C = 80W(\text{Max.})@T_C=25^\circ\text{C}$
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 100V(\text{Min.})$
- Complement to Type 2SA980

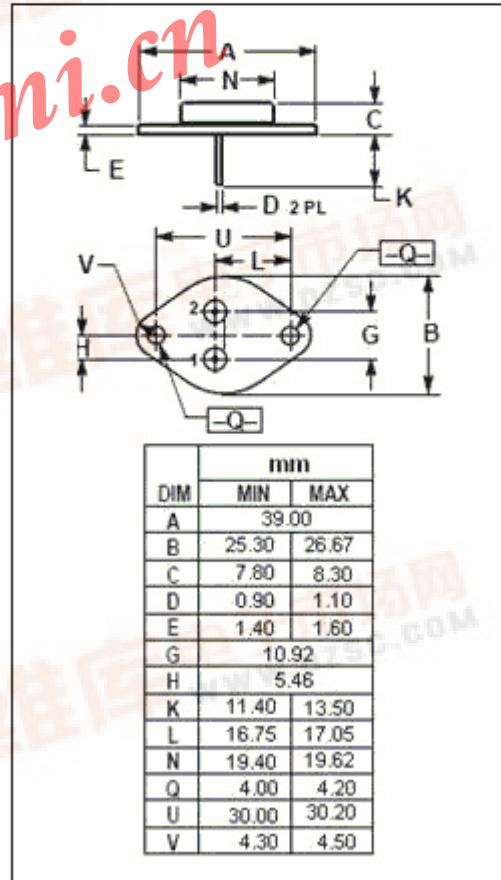
APPLICATIONS

- Designed for general purpose applications.



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	160	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	8	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$



## isc Silicon NPN Power Transistor

2SC2260

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 160V; I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	30			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.5A; V <sub>CE</sub> = 12V		15		MHz

[www.iscsemi.cn](http://www.iscsemi.cn)